

AMENDMENTS TO THE CLAIMS

This listing of claims will replace all prior versions and listings of claims in the application:

1-27. (Canceled)

28. (Original) A method for manufacturing a semiconductor device comprising:
forming a thin film integrated circuit by a droplet discharging method or a printing method over a first substrate;
forming an antenna over a second substrate; and
attaching the first substrate to the second substrate so that the thin film integrated circuit is electrically connected to the antenna.

29. (Original) The method for manufacturing a semiconductor device according to claim 28, wherein the antenna is formed by a sputtering method, a droplet discharging method, a printing method, a plating method, a photolithography method, or a vapor deposition method, using a metal mask.

30. (Original) The method for manufacturing a semiconductor device according to claim 28, wherein the antenna is formed by a sputtering method, a droplet discharging method, a printing method, a plating method, a photolithography method, or a vapor deposition method using a metal mask, and the antenna is pressed.

31. (Original) The method for manufacturing a semiconductor device according to claim 28, the method further comprising:

forming a metal film and an oxide film containing silicon over the metal film, between the first substrate and the thin film integrated circuit;

forming a metal oxide film comprising a metal included in the metal film on a surface of the metal film; and

separating the first substrate at an interface between the oxide and the metal film or an interface between the metal oxide film and the oxide film containing silicon.

32. (Original) A method for manufacturing a semiconductor device comprising:
forming a thin film integrated circuit by a droplet discharging method or a printing method over a first substrate in at least one step;
forming an antenna over a second substrate having flexibility; and
folding the second substrate to sandwich the thin film integrated circuit therebetween so that the thin film integrated circuit is electrically connected to the antenna.

33. (Original) The method for manufacturing a semiconductor device according to claim 32, wherein the antenna is formed by a sputtering method, a droplet discharging method, a printing method, a plating method, a photolithography method, or a vapor deposition method, using a metal mask.

34. (Original) The method for manufacturing a semiconductor device according to claim 32, wherein the antenna is formed by a sputtering method, a droplet discharging method, a printing method, a plating method, a photolithography method, or a vapor deposition method using a metal mask, and the antenna is pressed.

35. (Original) The method for manufacturing a semiconductor device according to claim 32, the method further comprising:

forming a metal film and an oxide film containing silicon over the metal film, between the first substrate and the thin film integrated circuit;

forming a metal oxide film comprising a metal included in the metal film on a surface of the metal film; and

separating the first substrate at an interface between the oxide and the metal film or an interface between the metal oxide film and the oxide film containing silicon.

36. (Original) A method for manufacturing a semiconductor device comprising:
forming a thin film integrated circuit by a droplet discharging method or a printing method over a first substrate in at least one step;
forming an antenna over a second substrate;
attaching the first substrate to the second substrate so that the thin film integrated circuit is electrically connected to the antenna; and

after attaching the first substrate to the second substrate, separating the first substrate from the thin film integrated circuit.

37. (Original) The method for manufacturing a semiconductor device according to claim 36, wherein the antenna is formed by a sputtering method, a droplet discharging method, a printing method, a plating method, a photolithography method, or a vapor deposition method, using a metal mask.

38. (Original) The method for manufacturing a semiconductor device according to claim 36, wherein the antenna is formed by a sputtering method, a droplet discharging method, a printing method, a plating method, a photolithography method, or a vapor deposition method using a metal mask, and the antenna is pressed.

39. (Original) The method for manufacturing a semiconductor device according to claim 36, the method further comprising:

forming a metal film and an oxide film containing silicon over the metal film, between the first substrate and the thin film integrated circuit;

forming a metal oxide film comprising a metal included in the metal film on a surface of the metal film; and

separating the first substrate at an interface between the oxide and the metal film or an interface between the metal oxide film and the oxide film containing silicon.

40. (Withdrawn) A method for manufacturing a semiconductor device comprising:

forming a thin film integrated circuit by a droplet discharging method or a printing method over a first substrate;

attaching a second substrate onto the thin film integrated circuit;

separating the first substrate from the thin film integrated circuit;

forming an antenna over a third substrate; and

attaching the second substrate to the third substrate so that the thin film integrated circuit is electrically connected to the antenna.

41. (Withdrawn) The method for manufacturing a semiconductor device according to claim 40, wherein the antenna is formed by a sputtering method, a droplet discharging method, a printing method, a plating method, a photolithography method, or a vapor deposition method, using a metal mask.

42. (Withdrawn) The method for manufacturing a semiconductor device according to claim 40, wherein the antenna is formed by a sputtering method, a droplet discharging method, a printing method, a plating method, a photolithography method, or a vapor deposition method using a metal mask, and the antenna is pressed.

43. (Withdrawn) The method for manufacturing a semiconductor device according to claim 40, the method further comprising:

forming a metal film and an oxide film containing silicon over the metal film, between the first substrate and the thin film integrated circuit;

forming a metal oxide film comprising a metal included in the metal film on a surface of the metal film; and

separating the first substrate at an interface between the oxide and the metal film or an interface between the metal oxide film and the oxide film containing silicon.

44. (Withdrawn) A method for manufacturing a semiconductor device comprising:

forming a thin film integrated circuit by a droplet discharging method or a printing method over a first substrate;

forming an antenna over the thin film integrated circuit;

attaching the first substrate to the second substrate so that the thin film integrated circuit is electrically connected to the antenna; and

separating the first substrate from the thin film integrated circuit.

45. (Withdrawn) The method for manufacturing a semiconductor device according to claim 44, wherein the antenna is formed by a sputtering method, a droplet discharging method, a printing method, a plating method, a photolithography method, or a vapor deposition method, using a metal mask.

46. (Withdrawn) The method for manufacturing a semiconductor device according to claim 44, wherein the antenna is formed by a sputtering method, a droplet discharging method, a printing method, a plating method, a photolithography method, or a vapor deposition method using a metal mask, and the antenna is pressed.

47. (Withdrawn) The method for manufacturing a semiconductor device according to claim 44, the method further comprising:

forming a metal film and an oxide film containing silicon over the metal film, between the first substrate and the thin film integrated circuit;

forming a metal oxide film comprising a metal included in the metal film on a surface of the metal film; and

separating the first substrate at an interface between the oxide and the metal film or an interface between the metal oxide film and the oxide film containing silicon.